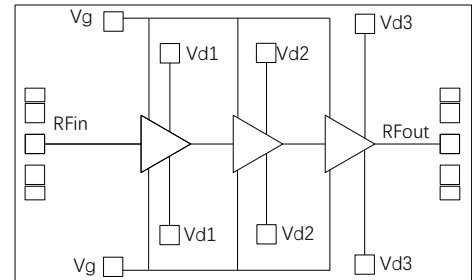


## GaN MMIC Power Amplifier Chip, 8.0-10.0 GHz

### Performance characteristics

- Frequency range: 8.0~10.0GHz
- Psat: 46dBm
- Power gain: 19dB
- Power supply: 28V/769mA
- 50ohm input/output
- Chip size:3.2mm×3.2mm×0.1mm

### Block Diagram



### Product Introduction

GPA8-10-46 is a power amplifier chip manufactured using GaN HEMT technology. The working frequency band covers 8.0-10.0GHz, and under a supply voltage of 28V, it can provide a power gain of 19dB with a saturated output power of 46dBm. The chip is grounded through the back through-hole. Mainly used in communication systems, high-power transceiver components, and other fields.

### DC electrical parameters (T<sub>A</sub>=+25°C)

Parameter	Min	Typ	Max	Unit
Gate bias voltage		-2.2		V
Drain working voltage		28		V
Quiescent drain current		769		mA
Dynamic drain current		3500		mA

### Microwave electrical parameters (T<sub>A</sub>=+25°C, V<sub>d</sub>=+28V, Pulse width 500us, Duty cycle 35%)

Parameter	Min	Typ	Max	Unit
Frequency range	8.0~10.0			GHz
Psat		46		dBm
PAE		40		%
Power gain		19		dB
Power gain flatness		±0.2		dB
Input/output return loss		-12		dB

### Absolute maximum ratings<sup>[1]</sup>

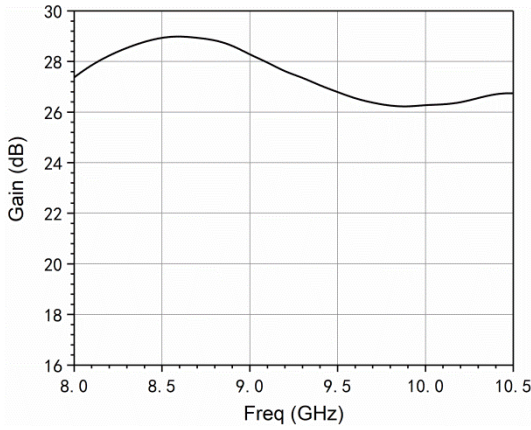
Parameter	Ratings
Drain voltage	+30V
Input power	+30dBm
Operating temperature	-55°C~+85°C
Storage temperature	-65°C~+120°C

[1] Exceeding any of these limits may cause permanent damage.

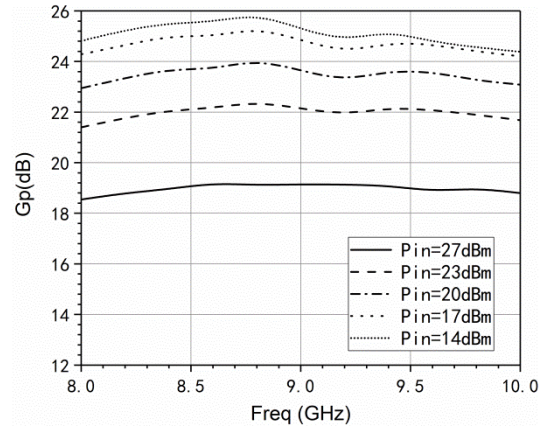
## GaN MMIC Power Amplifier Chip, 8.0-10.0 GHz

Typical performance curves (Vd: +28V, quiescent Id=769mA, pulse width 500us, duty cycle 35%)

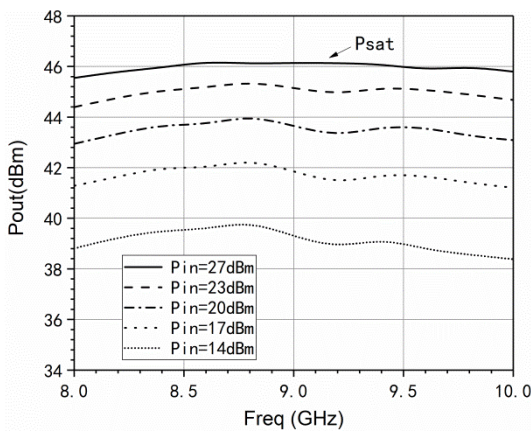
Gain vs. frequency (@Pin=-25dBm)



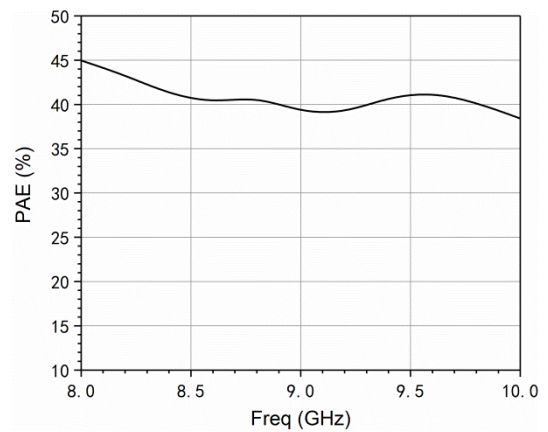
power gain vs. frequency



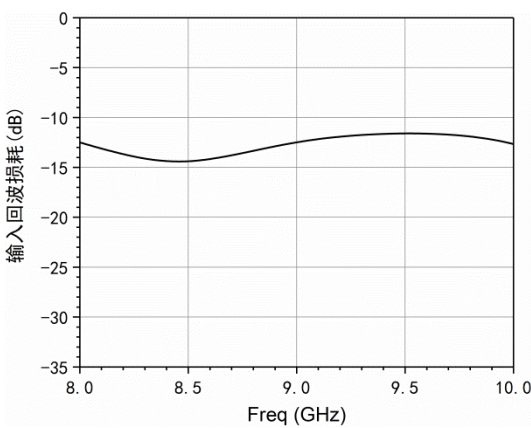
output power vs. frequency



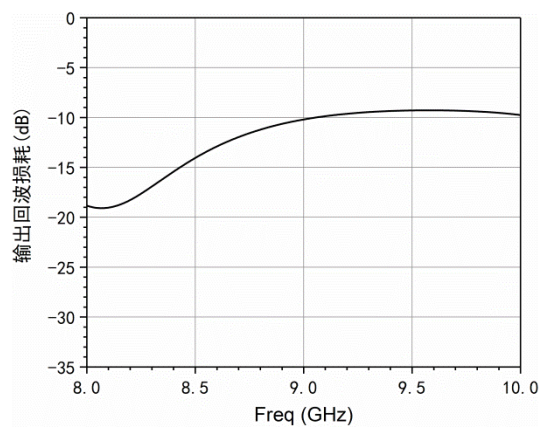
Power added efficiency vs. frequency (@ Pin=27dBm)



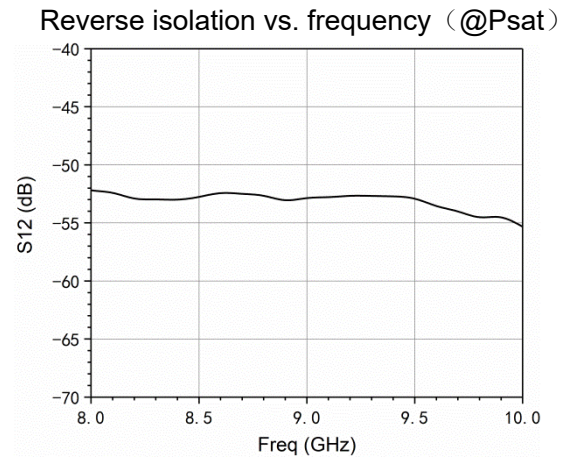
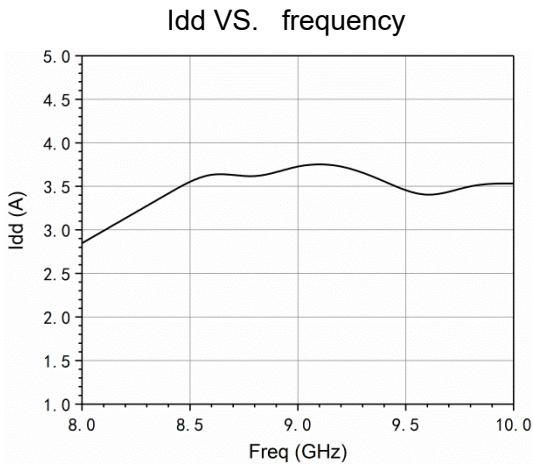
Input return loss vs. frequency



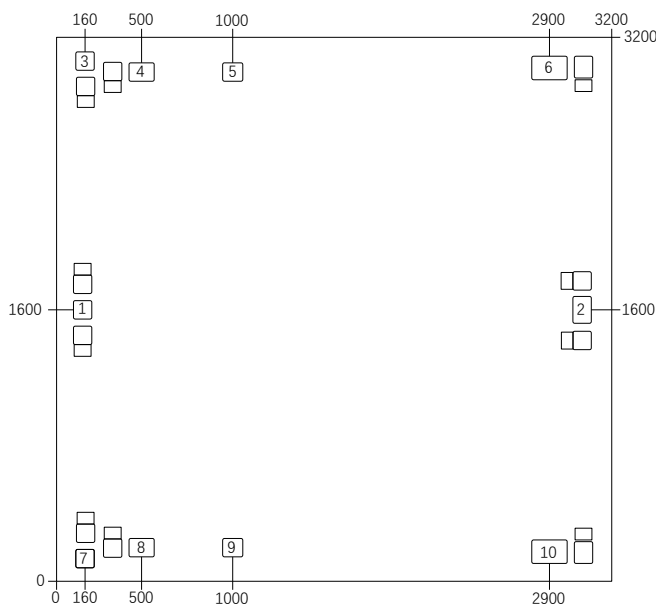
Output return loss vs. frequency



## GaN MMIC Power Amplifier Chip, 8.0-10.0 GHz



### Outline Dimensions



#### Notes:

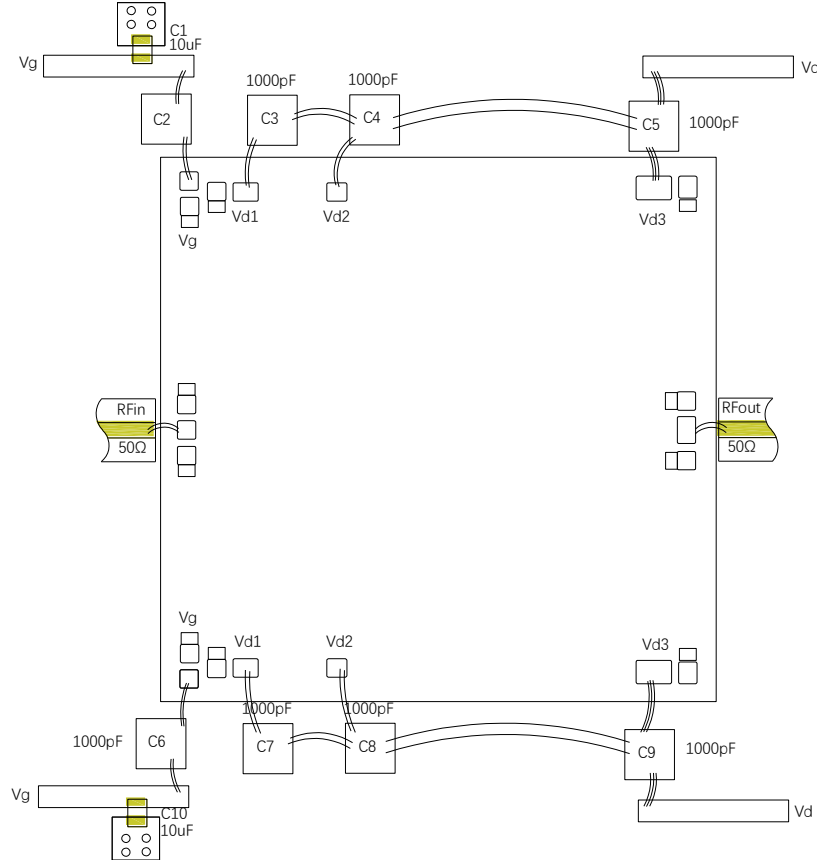
1. Unit:  $\mu\text{m}$
2. Gold plating on bonding pads
3. Dimensional tolerance:  $\pm 20 \mu\text{m}$

### Pad Definition

Pad Number	Function	Description	Dimensions
1	IN	RF input, external 50 ohm system, no need for external blocking capacitor	100 × 100 $\mu\text{m}$
2	OUT	RF output, external 50 ohm system, no need for external blocking capacitor	100 × 100 $\mu\text{m}$
4、5、6、8、9、10	V <sub>d</sub>	Drain power supply, 28V	100 × 100 $\mu\text{m}$
3、7	V <sub>g</sub>	Gate power supply, -2.2V, quiescent current 750-850mA	100 × 100 $\mu\text{m}$

## GaN MMIC Power Amplifier Chip, 8.0-10.0 GHz

### Suggested assembly diagram



Note: To ensure more stable performance of the amplifier, it is recommended to weld ceramic capacitors with the recommended capacitance values in the above assembly diagram at the feeding end for filtering. The number of filtering capacitors can also be increased or different capacitance values can be combined according to actual needs.

### Note:

1. Please assemble and use in a purified environment, store in anti-static containers, and keep dry
2. The back of the chip is grounded with gold backing. Please ensure that the back is in full contact with the ground and well grounded during use
3. Use gold tin solder with a ratio of 80/20 to sinter, with a sintering temperature not exceeding 300 °C and a sintering time as short as possible, not exceeding 20 seconds
4. This product is an electrostatic sensitive device. Please pay attention to anti-static measures during storage and use
5. Do not attempt to clean the surface of the chip using dry or wet chemical methods
6. If you have any questions, please contact the supplier

